

• General Description

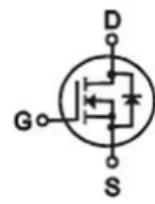
It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

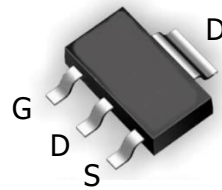
- SMPS 2nd Synchronous Rectifier
- BLDC Motor driver

• Product Summary


$V_{DS} = 100V$

$R_{DS(ON)} = 50m\Omega$

$I_D = 7.5A$



SOT-223

• Ordering Information:

Part NO.	ZMS420N10E
Marking	420N10
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^②	$I_D @ T_C = 25^\circ C$	7.5	A
	$I_D @ T_C = 75^\circ C$	5.7	A
	$I_D @ T_C = 100^\circ C$	4.7	A
Pulsed Drain Current ^①	I_{DM}	30	A
Total Power Dissipation ^②	$P_D @ T_C = 25^\circ C$	8	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	1	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy @ $L = 0.1mH$	E_{AS}	10	mJ
ESD Level (HBM)		1A	

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R _{thJC}	-	-	15	° C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	120	° C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	260	° C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.3		2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A		50	65	mΩ
	R _{DS(ON)}	V _{GS} =4.5V, I _D =6A		64	83	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =4A		4		s

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	f = 1MHz	-	275	-	pF
Output capacitance	C _{oss}		-	146	-	
Reverse transfer capacitance	C _{rss}		-	3.7	-	

Gate Charge characteristics(Ta= 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} =25V I _D = 8A V _{GS} = 10V	-	7	-	nC
Gate - Source charge	Q _{gs}		-	2.1	-	
Gate - Drain charge	Q _{gd}		-	1.1	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Gate-Charge Characteristics

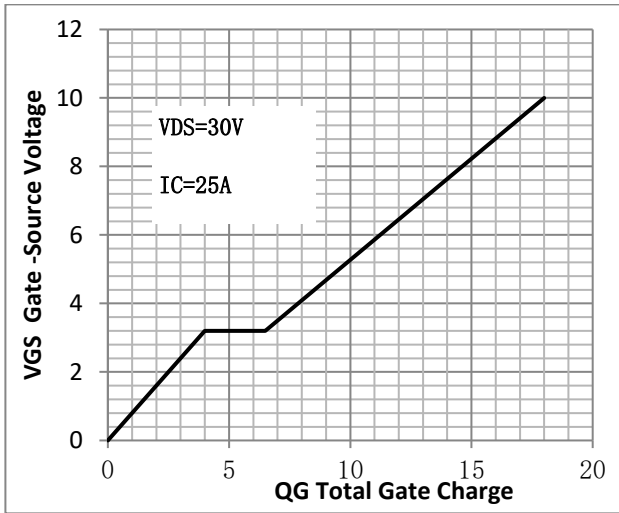


Fig.2 Capacitance Characteristics

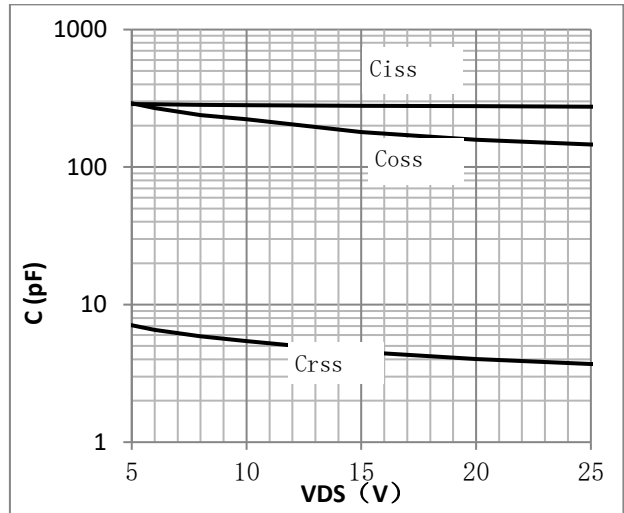


Fig.3 Power Dissipation

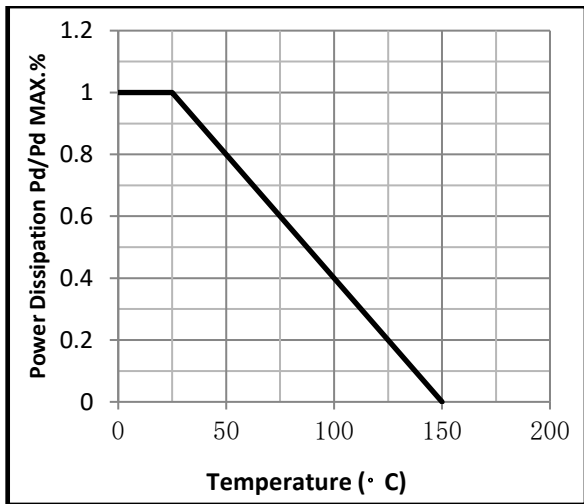


Fig.4 Typical output Characteristics

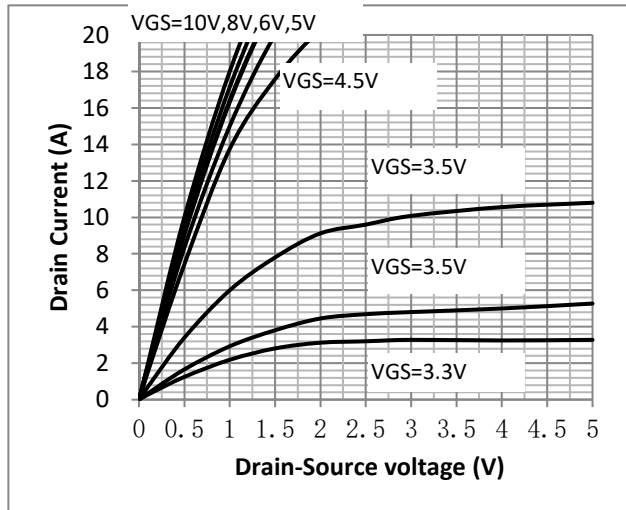


Fig.5 Threshold Voltage V.S Junction Temperature

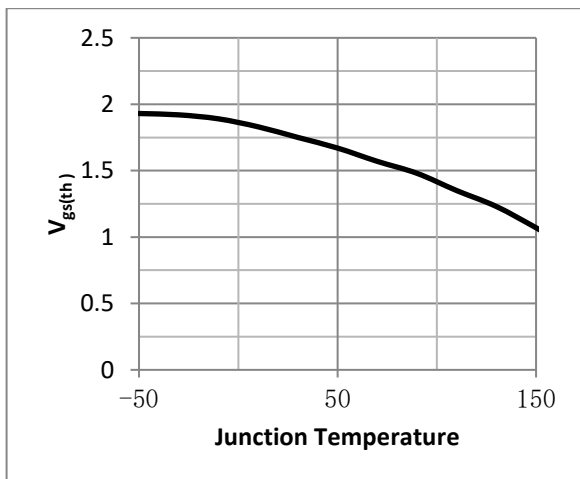


Fig.6 Resistance V.S Drain Current

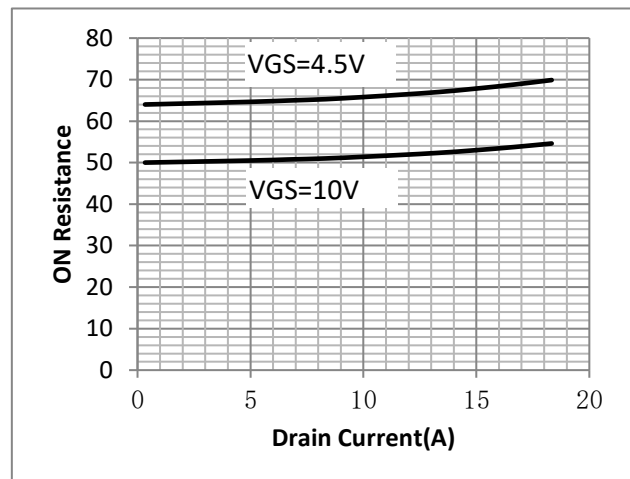


Fig.7 On-Resistance VS Gate Source Voltage

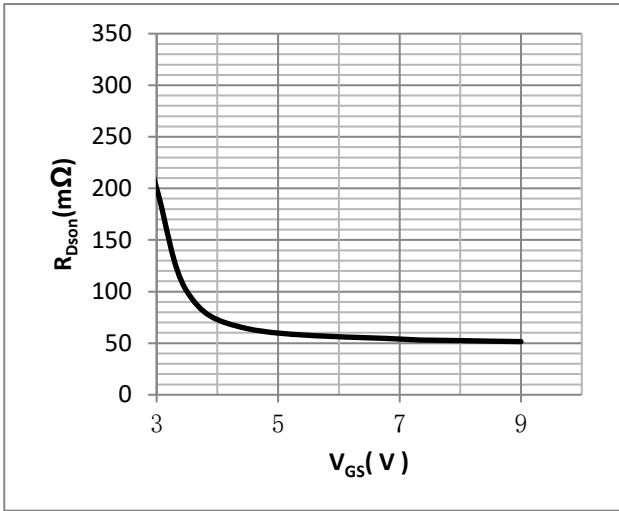


Fig.8 On-Resistance V.S Junction Temperature

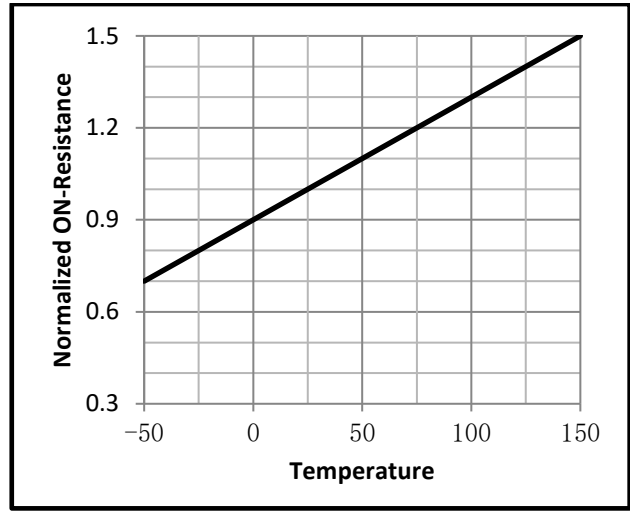


Fig.9 SOA Maximum Safe Operating Area

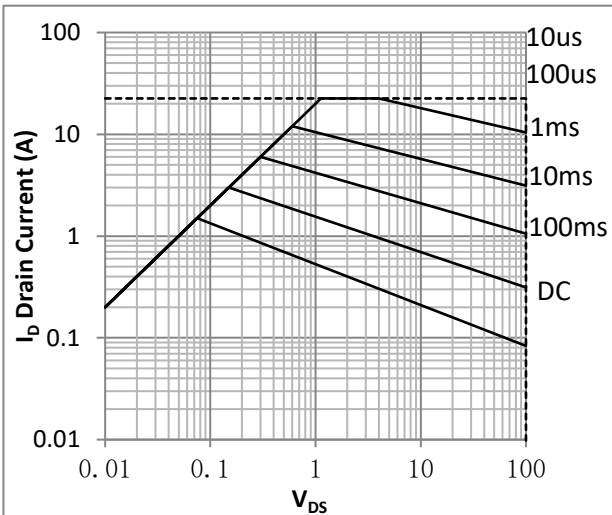


Fig.10 I_D-Junction Temperature

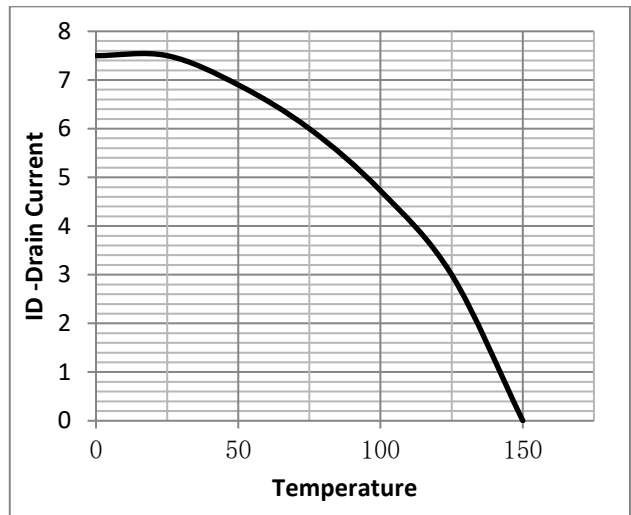


Figure 11. Diode Forward Voltage vs. Current

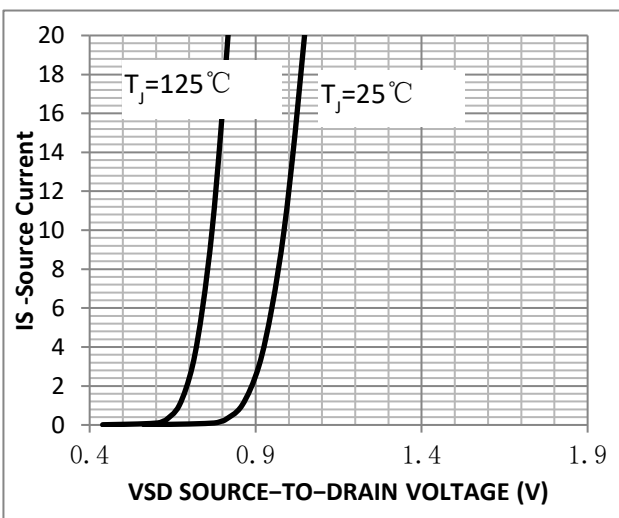


Figure 12. Transfer Characteristics

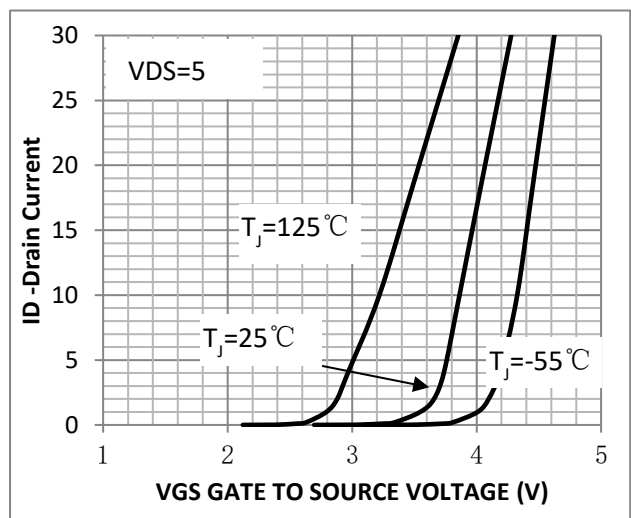


Fig.13 Switching Time Measurement Circuit

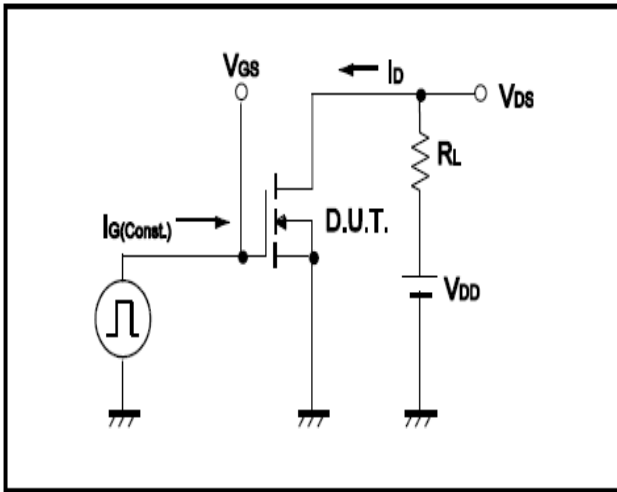


Fig.14 Gate Charge Waveform

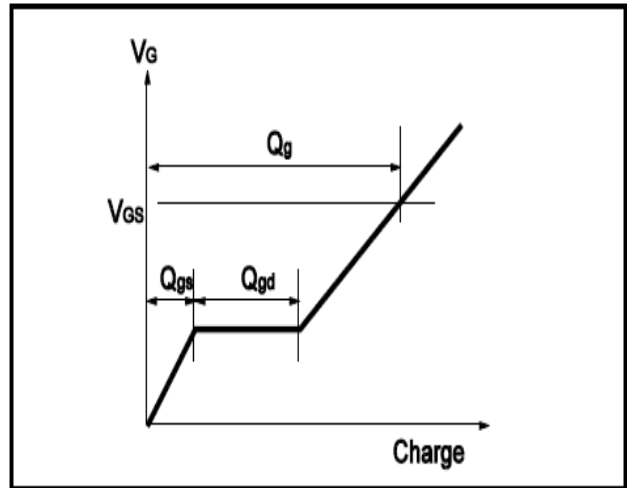


Fig.15 Switching Time Measurement Circuit

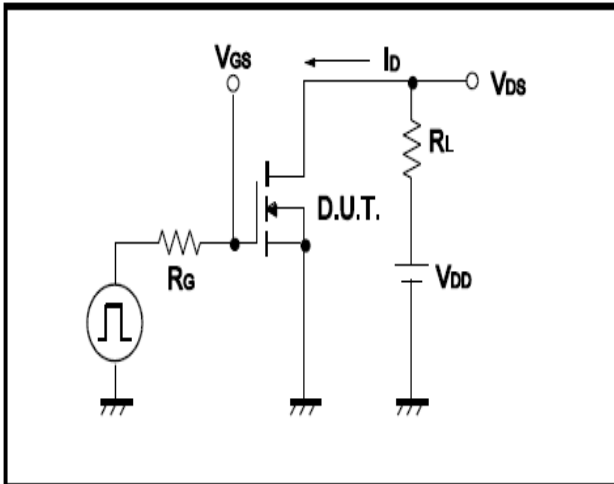
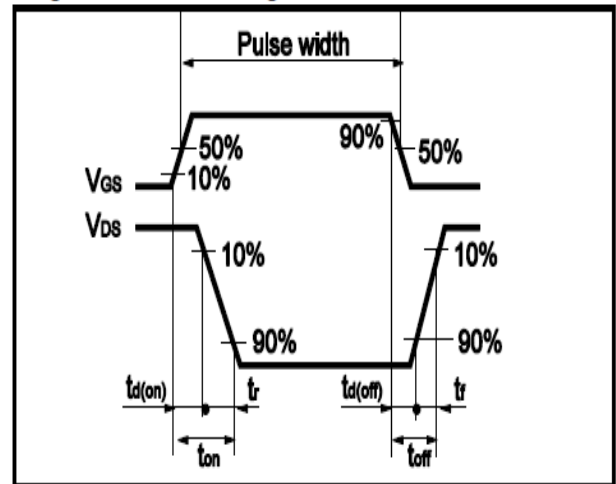


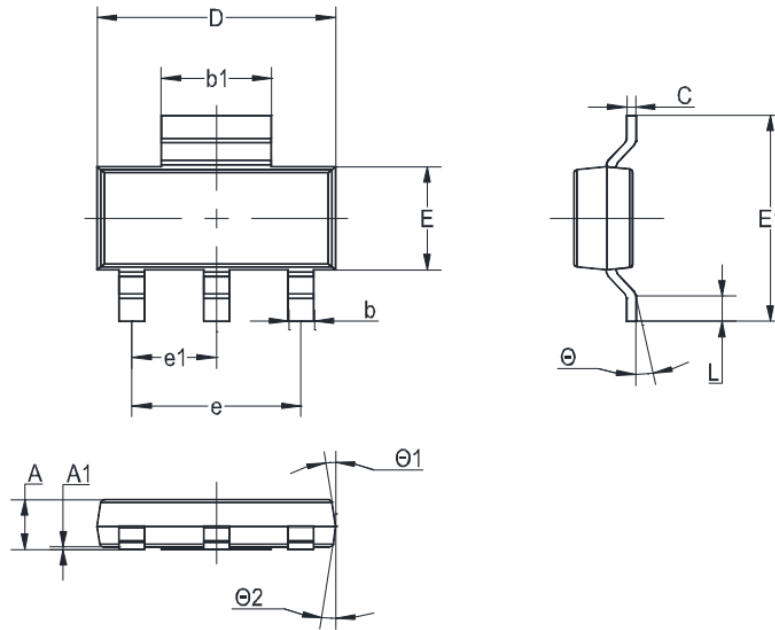
Fig.16 Gate Charge Waveform



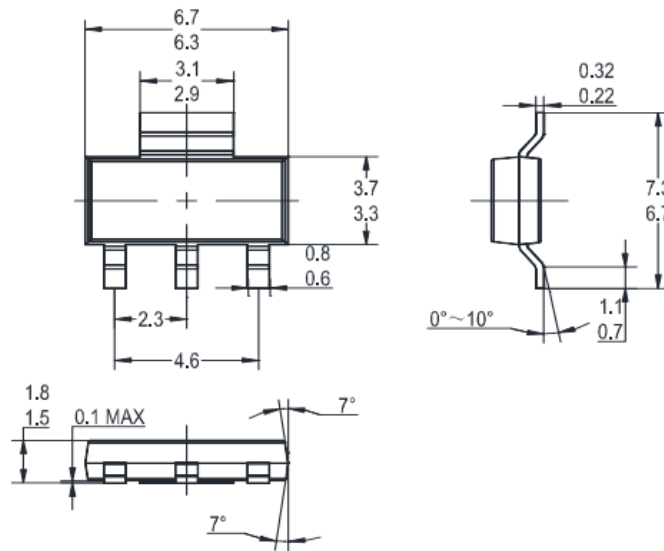


•Dimensions(SOT-223)

Unit: mm

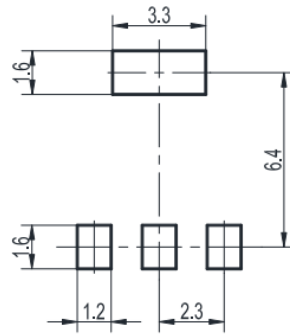


Unit	A	A1	b	b1	C	D	E	E1	e	e1	L	Θ	Θ1	Θ2
mm	1.8	0.1	0.8	3.1	0.32	6.7	3.7	7.3	4.6	2.3	1.1	10°	7°	7°
	1.5	MAX	0.6	2.9	0.22	6.3	3.3	6.7	TYP	TYP	0.7	0°	0°	0°





Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-223	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000